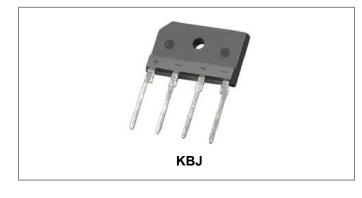


KBJ4005G THRU KBJ410G

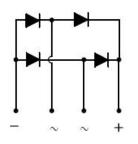
Technical Data Data Sheet N1818, Rev. A



KBJ4005G THRU KBJ410G GLASS PASSIVATED SINGLE-PHASE BRIDGE RECTIFIER



Circuit Diagram



Features

- Glass passivated chip junction KBJ
- Reliable low cost construction utilizing molded
 plastic technique
- Ideal for printed circuit board
- Low forward voltage drop
- Low reverse leakage current
- High surge current capability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Data

- Case: Molded plastic, KBJ
- Epoxy: UL 94V-O rate flame retardant
- Terminals: Leads solderable per MIL-STD-202, method 208 guaranteed
- Mounting position: Any
- Weight: 0.16ounce, 4.6gram

Maximum Ratings:@T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Type Number	Symbol	KBJ 4005G	KBJ 401G	KBJ 402G	KBJ 404G	KBJ 406G	KBJ 408G	KBJ 410G	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} Vdc	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Average forward rectified output current @Tc= 115°C	lo	4.0						А	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}				120				A

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KBJ4005G THRU KBJ410G

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Electrical Characteristics:@T_A=25°C unless otherwise specified

Type Number	Symbol	KBJ 4005G	KBJ 401G	KBJ 402G	KBJ 404G	KBJ 406G	KBJ 408G	KBJ 410G	Units
Forward Voltage (per element) @I _F =2A @I _F =4A	VF				1.0 1.1				V
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 125^{\circ}C$	I _{RM}				5.0 500				μA
Typical Junction Capacitance(per leg) (Note 1)	CJ				40				pF

* Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:@TA=25°C unless otherwise specified

Type Number	Symbol	KBJ 4005G	KBJ 401G	KBJ 402G	KBJ 404G	KBJ 406G	KBJ 408G	KBJ 410G	Units
Typical Thermal Resistance(Note 2)	R _{θJC}				5.5				°C/W
Operating and Storage Temperature Range	T _J , T _{STG}			-55	5 to +150				°C

Note: 1. Measured at 1 MHZ and applied reverse voltage of 4.0 VDC.

2. Thermal Resistance from Junction to Case with Device Mounted on 75mm x 75mm x 1.6mm Cu Plate Heatsink.

Ratings and Characteristics Curves



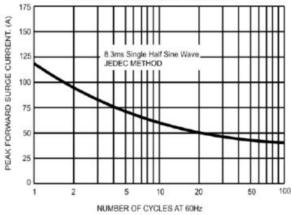
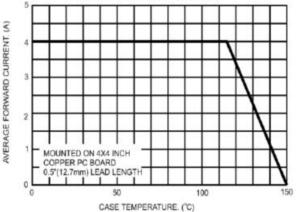


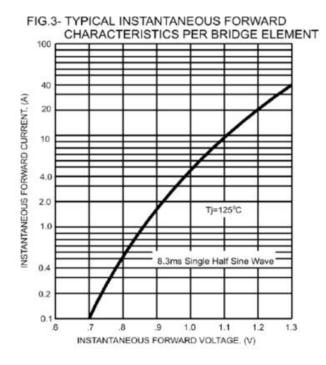
FIG.2- MAXIMUM FORWARD CURRENT DERATING CURVE PER BRIDGE ELEMENT

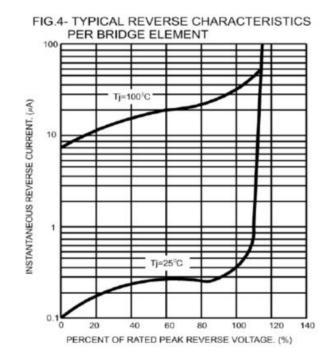






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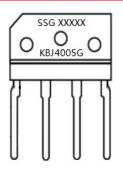




Ordering Information

Device	Package	Plating	Shipping
KBJ4005G THRU KBJ410G	KBJ (Pb-Free)	Pure Sn	20pcs / Tube

Marking Diagram



Where XXXXX is YYWWL	_
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SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number
KBJ4005G	= Type Number

Cautions: Molding resin Epoxy resin UL:94V-0

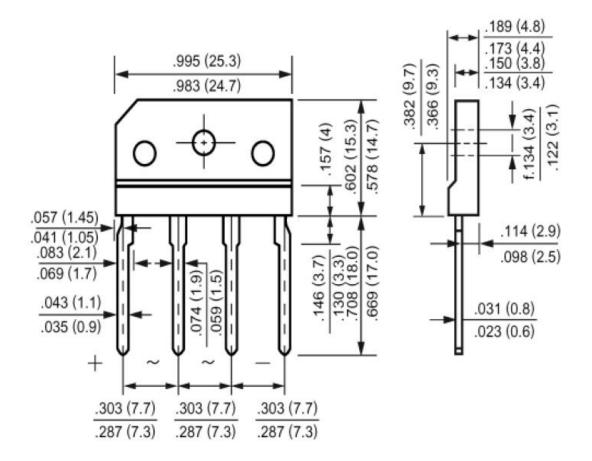
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Mechanical Dimensions KBJ (Inches/Millimeters)









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